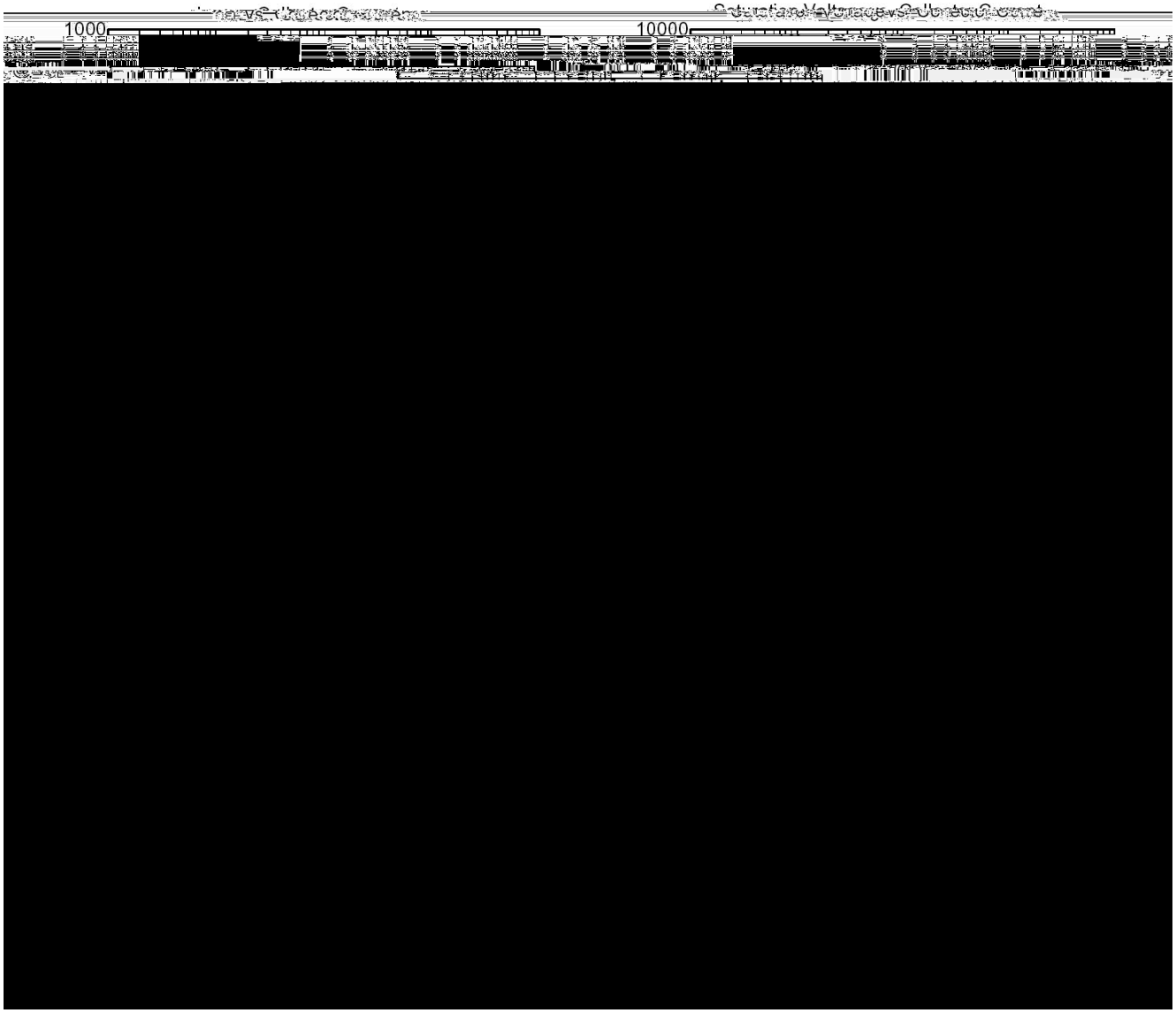
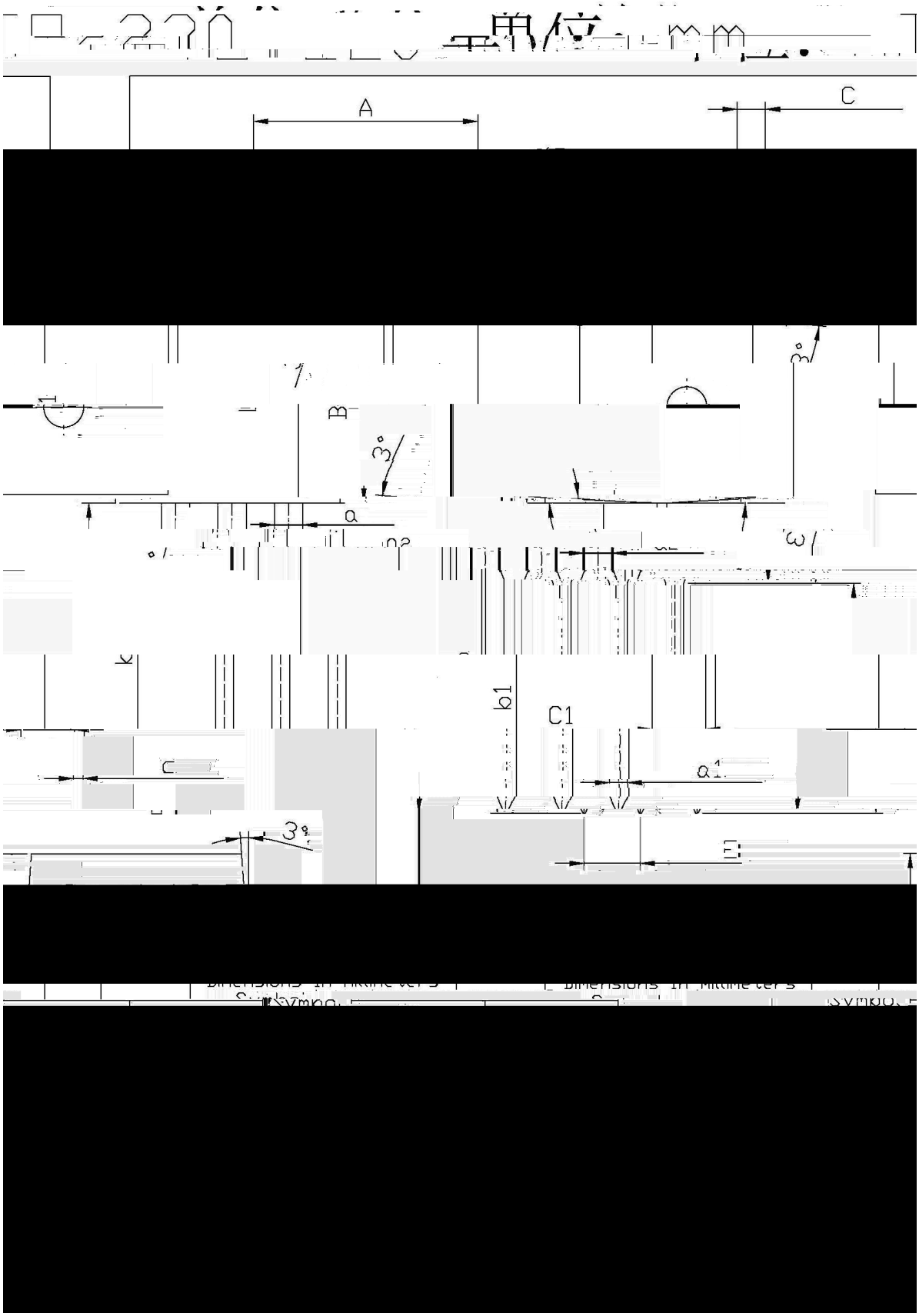
v ˝Ω Parameter	˧ ᴺ Symbol	˝ΩӨ Rating	ᴅ Ᵹ Unit
Collector to Base Voltage	V_{CBO}	-70	V
Collector to Emitter Voltage	V_{CEO}	-50	V
Emitter to Base Voltage	V_{EBO}	-5.0	V
Collector Current - Continuous	I_C	-4.0	A
Base Current - Continuous	I_{CP}	-8.0	A
Collector Power Dissipation	$P_C(T_C=25\quad)$	40	W
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

v ˝Ω Parameter	˧ ᴺ Symbol	╜ ፡ᛏ ᛠ Test Conditions	ῳ ꞑ Ӫ Min	Ɛ ʒ Ө Typ	ῳ ᶻ Ө Max	ᴅ Ᵹ Unit
Collector to Base Breakdown Voltage	V_{CBO}	I_C=-10 A I_E=0	-70			V
Collector to Emitter Breakdown Voltage	V_{CEO}	I_C=-50mA I_B=0	-50			V
Emitter to Base Breakdown Voltage	V_{EBO}	I_E=-10 A I_C=0	-5.0			V
Collector Cut-Off Current	I_{CBO}	V_{CB}=-50V I_E=0			-1.0	A
DC Current Gain	$h_{FE(1)*}$	V_{CE}=-4.0V I_C=-1.0A*	60		320	
	$h_{FE(2)*}$	V_{CE}=-4.0V I_C=-0.1A*	35			
Collector to Emitter Saturation Voltage*	$V_{CE(sat)*}$	I_C=-2.0A I_B=-0.2A*			-1.0	V
Base to Emitter Voltage*	V_{BE*}	V_{CE}=-4.0V I_C=-1.0A*			-1.0	V
Transition Frequency*	f_{T*}	V_{CE}=-4.0V I_C=-0.5A*				

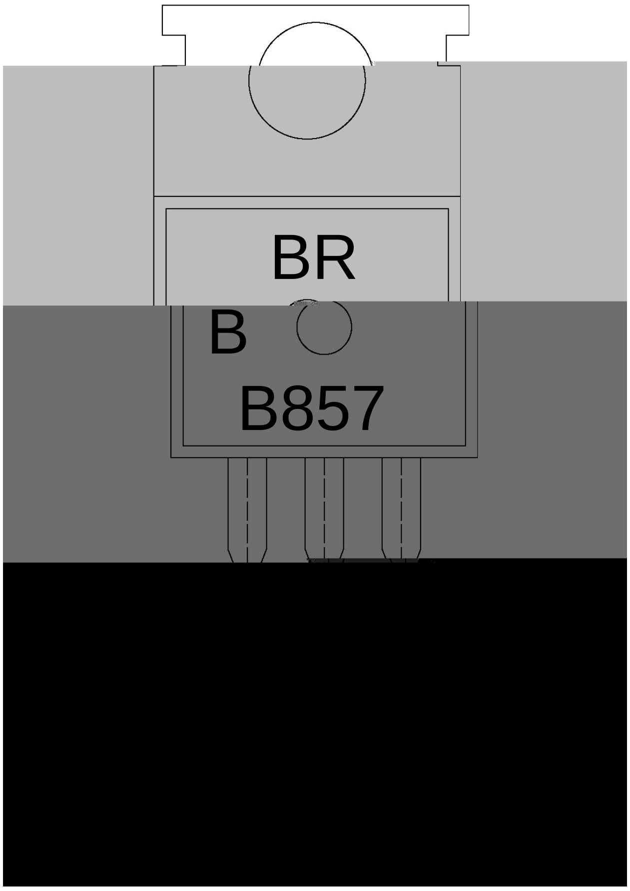
/ Electrical Characteristic Curve



/ Package Dimensions



/ Marking Instructions



ب ˝ χ

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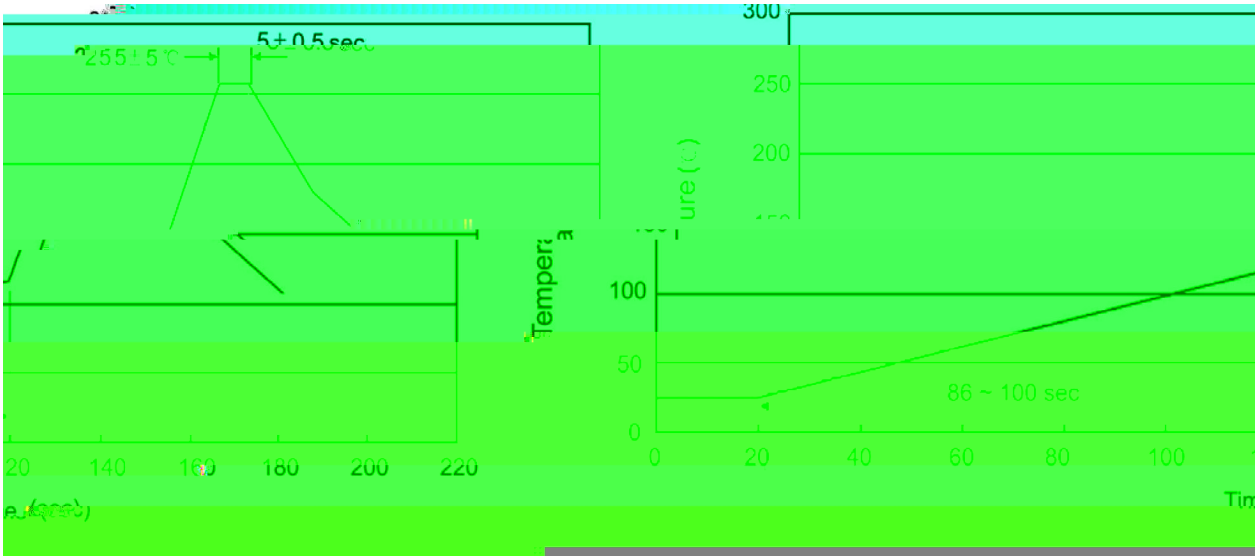
E꞊ ꞁꭗ k ꞁ ʜ ˂ ⁶ Ⴆ

- - - - χ ꞁꭗ ꜝ ꞙ ῆ ᴺ Ⴆ ꞁ ꞓ ꜝ ꞙ ῆ ᴺ ψ ꟼ

Note:

BR:	Company Code
B857:	Product Type.
B:	h_{FE} Classifications Symbol
****:	Lot No. Code, code change with Lot No.

( ) / Temperature Profile for Dip Soldering(Pb-Free)



ب ˝ χ

1 Ĺ ♬ □ ỷ 25 Ḱ 150 ł ı ˋH ڑ 60 Ḱ 90sec;

2 Š Ө □ ỷ 255 ° 5 ł ı ˋH ڑ ˋY ﾊ ㎛ 5 ° 0.5sec;

3 ì ˙ ﾘ ˛ ɔ ﷺ ỷ ㎛ 2 Ḱ 10 ł /sec.

Note:

1.Preheating:25~150 ł , Time:60~90sec.

2.Peak Temp.:255 ° 5 ł , Duration:5 ° 0.5sec.

3. Cooling Speed: 2~10 ł /sec.

/ Resistance to Soldering Heat Test Conditions

□ ỷ χ 270 ° 5 ł	ˋH ڑ χ 10 ° 1 sec.	Temp.:270±5	Time:10±1 sec

/ Packaging SPEC.

ˇQ ţ ﾘ Ł / BULK

Package Type 封装形式	Units 包装数量			Dimension 包装尺寸 (unit: mm^3)
	只袋	袋盒	只盒	

金Dur73.7teT4 1 Tfo 0 0 6.48 247.7431-0.9603 Tm0 28Tc0 Tw( )TjETQT/TT13 1 31-0.9600 0 6.48 222.3 283.0403 Tr